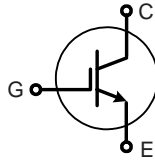
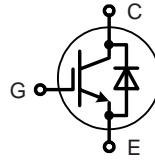


## NPT<sup>3</sup> IGBT

$$\begin{aligned} I_{C25} &= 60 \text{ A} \\ V_{CES} &= 1200 \text{ V} \\ V_{CE(sat) \text{ typ.}} &= 2.4 \text{ V} \end{aligned}$$

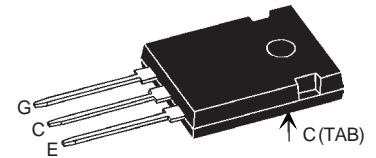


IXEH 40N120



IXEH 40N120D1

TO-247 AD



IGBT			
Symbol	Conditions	Maximum Ratings	
$V_{CES}$	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	1200	V
$V_{GES}$		$\pm 20$	V
$I_{C25}$	$T_C = 25^{\circ}\text{C}$	60	A
$I_{C90}$	$T_C = 90^{\circ}\text{C}$	40	A
$I_{CM}$ $V_{CEK}$	$V_{GE} = \pm 15 \text{ V}; R_G = 39 \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	50 $V_{CES}$	A
$t_{SC}$ (SCSOA)	$V_{CE} = 900\text{V}; V_{GE} = \pm 15 \text{ V}; R_G = 39 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	$\mu\text{s}$
$P_{tot}$	$T_C = 25^{\circ}\text{C}$	300	W

### Features

- NPT<sup>3</sup> IGBT
  - low saturation voltage
  - positive temperature coefficient for easy paralleling
  - fast switching
  - short tail current for optimized performance in resonant circuits
- optional HiPerFRED™ diode
  - fast reverse recovery
  - low operating forward voltage
  - low leakage current
- TO-247 package
  - industry standard outline
  - epoxy meets UL 94V-0

### Applications

- AC drives
- DC drives and choppers
- Uninterruptible power supplies (UPS)
- switched-mode and resonant-mode power supplies
- inductive heating, cookers

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 40 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.4 2.8	3.0 V
$V_{GE(th)}$	$I_C = 1 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
$I_{CES}$	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.4	0.4 mA mA
$I_{GES}$	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			200 nA
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $E_{on}$ $E_{off}$	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 40 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 39 \Omega$		85 50 440 50 6.1 3.0	ns ns ns ns mJ mJ
$C_{ies}$			2	nF
$Q_{Gon}$			250	nC
$R_{thJC}$				0.42 K/W

## Diode [D1 version only]

Symbol	Conditions	Maximum Ratings	
$I_{F25}$	$T_C = 25^\circ\text{C}$	60	A
$I_{F90}$	$T_C = 90^\circ\text{C}$	35	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$V_F$	$I_F = 40\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		2.6 2.0	3.0 V
$I_{RM}$ $t_{rr}$ $E_{rec(off)}$	$I_F = 30\text{ A}; di_F/dt = -500\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 600\text{ V}; V_{GE} = 0\text{ V}$		51 180 1.8	A ns mJ
$R_{thJC}$				1.0 K/W

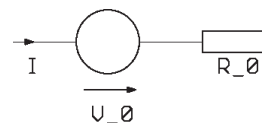
## Component

Symbol	Conditions	Maximum Ratings	
$T_{VJ}$		-55...+150	$^\circ\text{C}$
$T_{stg}$		-55...+150	$^\circ\text{C}$
$M_d$	mounting torque	0.8...1.2	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{thCH}$	with heatsink compound		0.25	K/W
Weight			6	g

## Equivalent Circuits for Simulation

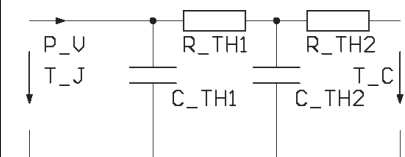
## Conduction



IGBT (typ. at  $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$ )  
 $V_0 = 0.95\text{ V}; R_0 = 45\text{ m}\Omega$

Diode (typ. at  $T_J = 125^\circ\text{C}$ )  
 $V_0 = 1.26\text{ V}; R_0 = 15\text{ m}\Omega$

## Thermal Response



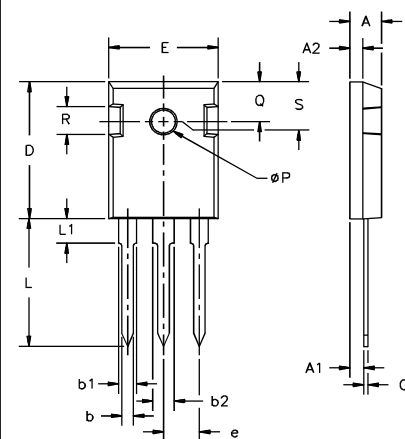
## IGBT

$C_{th1} = 0.007\text{ J/K}; R_{th1} = 0.215\text{ K/W}$   
 $C_{th2} = 0.187\text{ J/K}; R_{th2} = 0.205\text{ K/W}$

## Diode

$C_{th1} = 0.006\text{ J/K}; R_{th1} = 0.649\text{ K/W}$   
 $C_{th2} = 0.113\text{ J/K}; R_{th2} = 0.351\text{ K/W}$

## TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

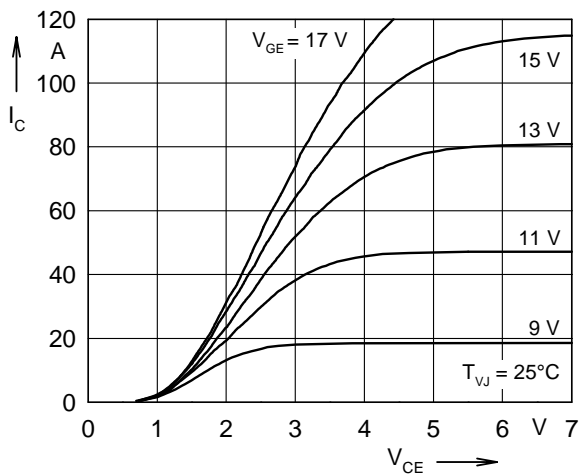


Fig. 1 Typ. output characteristics

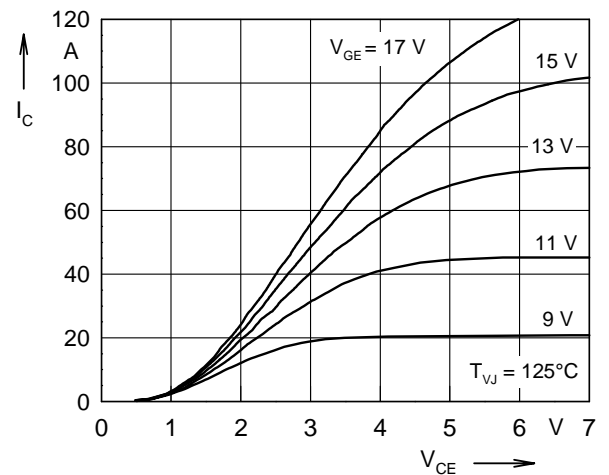


Fig. 2 Typ. output characteristics

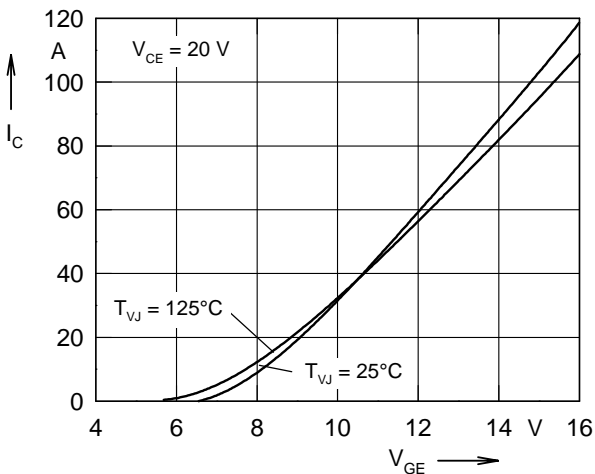


Fig. 3 Typ. transfer characteristics

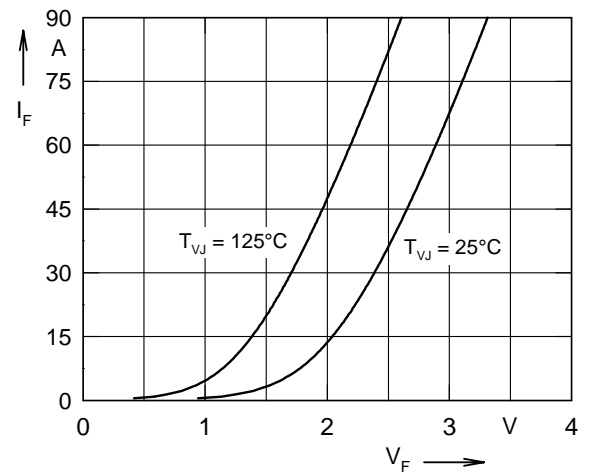


Fig. 4 Typ. forward characteristics of free wheeling diode

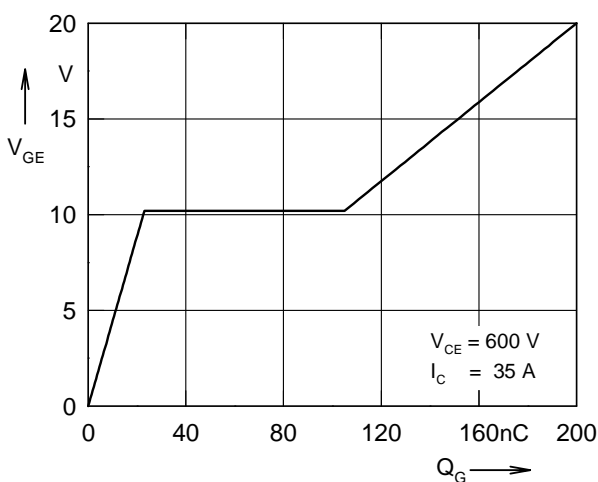


Fig. 5 Typ. turn on gate charge

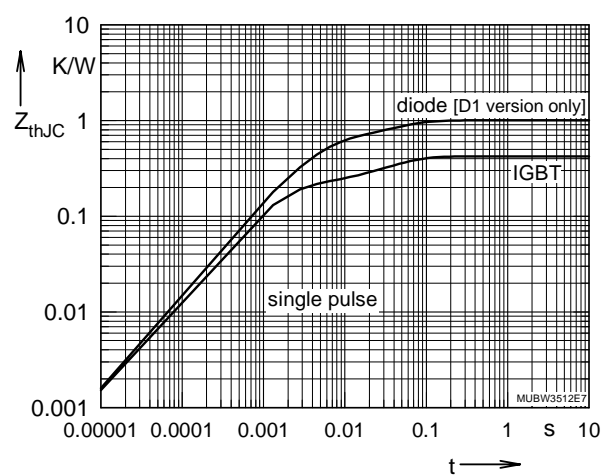


Fig. 6 Typ. transient thermal impedance

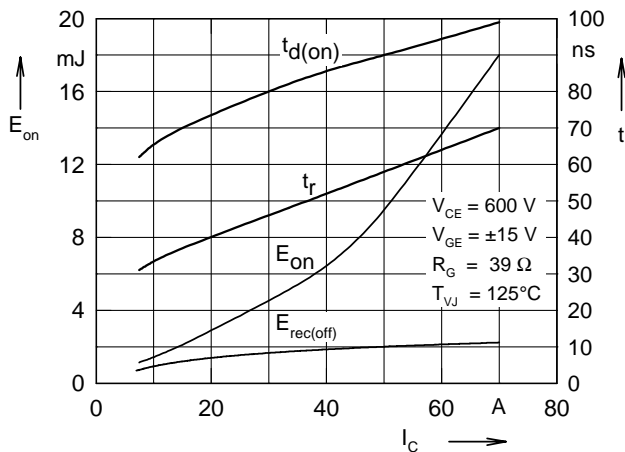


Fig. 7 Typ. turn on energy and switching times versus collector current

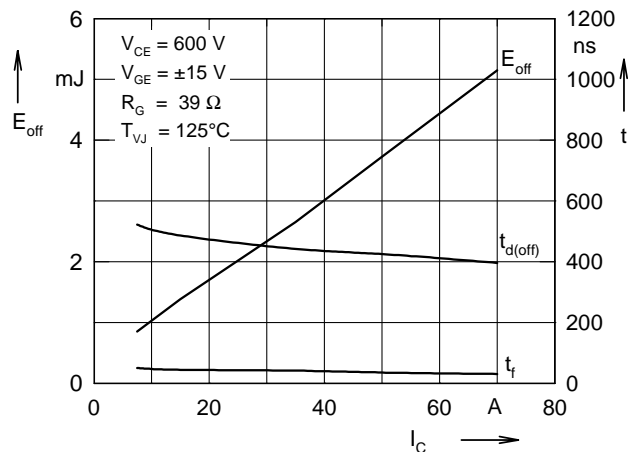


Fig. 8 Typ. turn off energy and switching times versus collector current

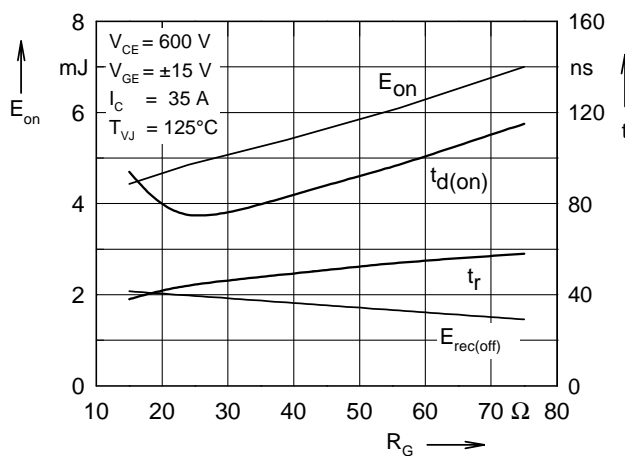


Fig. 9 Typ. turn on energy and switching times versus gate resistor

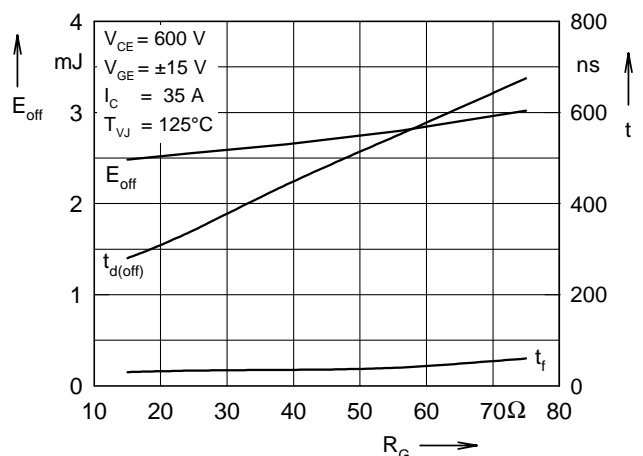


Fig. 10 Typ. turn off energy and switching times versus gate resistor

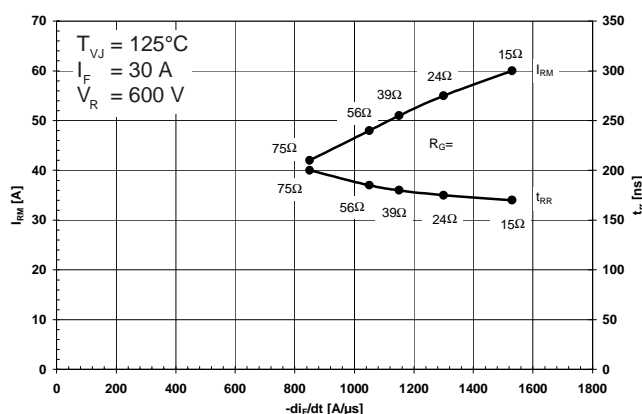


Fig. 11 Typ. turn off characteristics of free wheeling diode

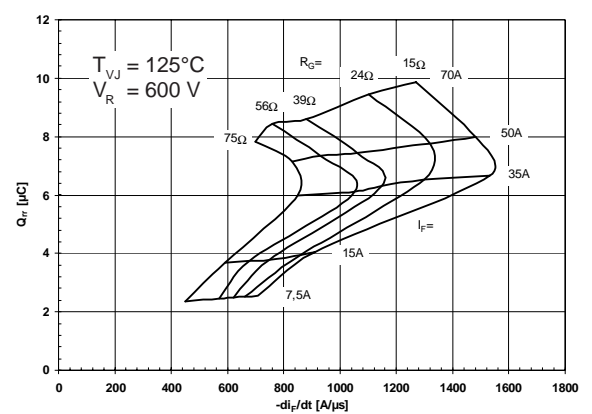


Fig. 12 Typ. turn off characteristics of free wheeling diode